

VERSION WITH MARKINGS TO SHOW CHANGES MADE**IN THE CLAIMS**

Claim 26 has been canceled.

Claims 27-30 and 33-39 have been amended as follows.

27. (Amended) The film acoustic wave device according to claim [26]41, wherein a length of the upper electrode is changed by the position at the wafer.

28. (Amended) The film acoustic wave device according to claim [26]41, wherein a width of the upper electrode is changed by the position at the wafer.

29. (Amended) The film acoustic wave device according to claim [26]41, wherein the upper electrode includes a plurality of upper electrodes, wherein distances between the upper electrodes are changed by the position at the wafer.

30. (Amended) The film acoustic wave device according to claim [26]41, further comprising a bonding pad for connecting with the upper electrode, wherein a shape of the bonding pad is changed by the position at the wafer.

33. (Amended) The film acoustic wave device according to claim [26]41, further comprising a capacitor provided on the same semiconductor substrate as the film acoustic wave device, wherein a capacitance of the capacitor is changed by the position of the wafer.

34. (Amended) The film acoustic wave device according to claim [26]41, wherein the semiconductor substrate is made of gallium arsenide (GaAs); the piezoelectric thin film is made of lead titanate (PbTiO_3); and at least one of the upper electrode is a conductor substantially made of platinum (Pt).

35. (Amended) The film acoustic wave device according to claim [26]41, wherein the a semiconductor substrate is made of silicon (Si); the piezoelectric thin film is made of lead titanate (PbTiO_3); and at least one of the upper electrode is a conductor substantially made of platinum (Pt).

36. (Amended) The film acoustic wave device according to claim [26]41, wherein the piezoelectric thin film is made of PZT (PbTiO_3 - PbZrO_3); and at least one of the upper electrode and the ground electrode is a conductor substantially made of platinum (Pt).

37. (Amended) The film acoustic wave device according to claim [26]41, wherein the piezoelectric thin film is made of zinc oxide (ZnO).

38. (Amended) The film acoustic wave device according to claim [26]41, wherein the piezoelectric thin film is made of aluminum nitride (AlN).

39. (Amended) The film acoustic wave device according to claim [26]41, further comprising an inductor between the semiconductor substrate and the ground electrode.

Claim 41 has been added.